GaN Hybrid Power Amplifier HR5459-25B

Product Features

- GaN on SiC HEMT
- Surface Mount Hybrid Type
- Compact Size & Mass
- High Efficiency
- Low Cost
- Custom design available

Applications

- Radar Systems
- Pulse amplifier application





Description

The HR5459-25B is designed for Radar system application frequencies from 5.4GHz to 5.9GHz and GaN HEMT technology has been used that performs high breakdown voltage, wide bandwidth and high efficiency. HR5459-25B has been designed 2 stages to have higher Gain at the wide frequency range of 5.4GHz ~ 5.9 GHz. GaN HEMT technology has been used to every amplifier in it for better reliability. Since it is high efficiency amplifier, it can perform at max 10% duty cycle and 50us of pulse width.

PARAMETER		UNIT	MIN	ТҮР	MAX	CONDITION
Frequency Range		MHz	5400	-	5900	ZS = ZL = 50 ohm
Power Gain			15	18		
Power	Flatness	dB	-	-	1	Amp: Idq1 = 10mA
Input Return Loss			-	-6	-	Idq2 = 10mA
Pout @ Psat		W	20	25)	
Harmonics 1 to N		dBc	-	-25	-	-
Pulse Droop		dB		0.5	1	-
Pulse Fall Time		ns		n I C	200	
Response	Rise Time	ns			200	-
Drain Efficiency		%	40	45	-	Davit @ Davit
Ids		А	-	1.25	1.35	Pout @ Peak
Supply Voltage		V	-3.5	-3.3	-2.7	Gate Bias (Vgs1 and Vgs2)
		V	-	50	-	Main Bias(Vds)

Electrical Specifications @ Vds =50V, Ta=25 °C

Caution

The drain voltage must be supplied to the device after the gate voltage is supplied

Turn on : Turn on the Gate Voltage supply and last turn On the Drain voltage supplies

Turn off : Turn off the Drain Voltage and last turn off the Gate voltage

Test condition = 50us (pulse width), 10%(duty cycle), Pin=26dBm

Note

HR Series have internal DC blocking capacitors at the RF input and output ports

Mechanical Specifications

PARAMETER UNIT		ТҮР	REMARK	
Mass	g	2	-	
Dimension	mm	20.5 x 12.5 x 4.8	-	

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Absolute Maximum Ratings

PARAMETER	UNIT	RATING	SYMBOL
Gate-Source Voltage	V	-10 ~ 0	Vgs1 Vgs2
Drain-Source Voltage	Drain-Source Voltage V 84		Vds
Gate Current	mA	5.7	Ig
Operating Junction Temperature	°C	225	TJ
Operating Case Temperature	°C	-20 ~ 85	Tc
Storage Temperature	°C	$-40 \sim 100$	T _{STG}

Operating Voltages

PARAMETER	UNIT	MIN	ТҮР	MAX	SYMBOL
Drain Voltage	V	-	50	-	Vds
Gate Voltage (on-stage)	V	-	Vgs1@Idq1	-2	Vgs 1
Gate Voltage (on-stage)	V	_	Vgs2@Idq2	-2	Vgs 2
Gate Voltage (off-stage)	V	-	-8	-	Vgs 1
Gate Voltage (off-stage)	V	-	-8	_	Vgs 2

Power Supply

PARAMETER	UNIT	MIN	ТҮР	MAX	SYMBOL
Drain-Source current	А	rth	6 .00	2	Ids
Gate-Source Current (on-stage)	mA		C.CO	20	Igs
Gate-Source Current (off-stage)	mA	-	-	0.04	Igs

Block Diagram



HR5459-25B



Application Circuit



RFH

Package Dimensions (Type: NP-36B)

* Unit: mm[inch] | Tolerance: ±0.15[.006]



▲ Top View ▲ Side View

Pin No	Function	Pin No	Function
1	Vds1	6	Vds2
2	RF input	5	RF output
3	Vgs1	4	Vgs2

Recommended Pattern



* Mounting Configuration Notes

- 1. For the proper performance of the device, Ground / Thermal via holes must be designed to remove heat.
- 2. To properly use heatsink, ensure the ground/thermal via hole region to contact the heatsink. We recommend the mounting screws be added near the heatsink to mount the board
- 3. In designing the necessary RF trace, width will depend upon the PCB material and construction.
- 4. Use 1 oz. Copper minimum thickness for the heatsink.
- 5. Do not put solder mask on the backside of the PCB in the region where the board contacts the heatsink
- 6. We recommend adding as much copper as possible to inner and outer layers near the part to ensure optimal thermal performance.



Precautions

This product is a Gallium Nitride Transistor.

The Gallium Nitride Transistor requires a Negative Voltage Bias which operates alongside a Positive Voltage Bias. These Biases are applied in accordance to the Sequence during Turn-On and Turn-Off.

The Pallet Amplifier does not have a built-in Bias Sequence Circuit. Therefore, users need to either apply positive voltages and negative voltages in the required sequence, or add an external Bias Circuit to this Amplifier. The required sequence for power supply is as follows.

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During Turn-On

- 1. Connect GND.
- 2. Apply Vgs1 and Vgs2.
- 3. Apply Vds.
- 4. Apply the RF Power.



Ordering Information

Part Number	Package Design	
	-R (Reel)	
HR5459-25B	-B (Bulk)	
	-EVB (Evaluation Board)	

Revision History

Part Number	Release Date	Version	Modification	Data Sheet Status
HR5459-25B	2017.12.01	1.2	Changed recommended pattern & LID Type	-
HR5459-25B	2014.04.07	1.1	Changed Specification	-
HR5459-25B	2013.04.02	0.5	Changed Specification	Preliminary
HR5459-25B	2013.03.15	0.4	The first written document	Preliminary



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